



Technical Data Sheet

5mm Infrared LED, T-1 3/4

HIR333

Features

- High reliability
- High radiant intensity
- Peak wavelength $\lambda_p=850\text{nm}$
- 2.54mm Lead spacing
- Low forward voltage
- Pb free
- The product itself will remain within RoHS compliant version.

Descriptions

- EVERLIGHT'S Infrared Emitting Diode(HIR333) is a high intensity diode , molded in a yellow transparent plastic package.
- The device is spectrally matched with phototransistor , photodiode and infrared receiver module.



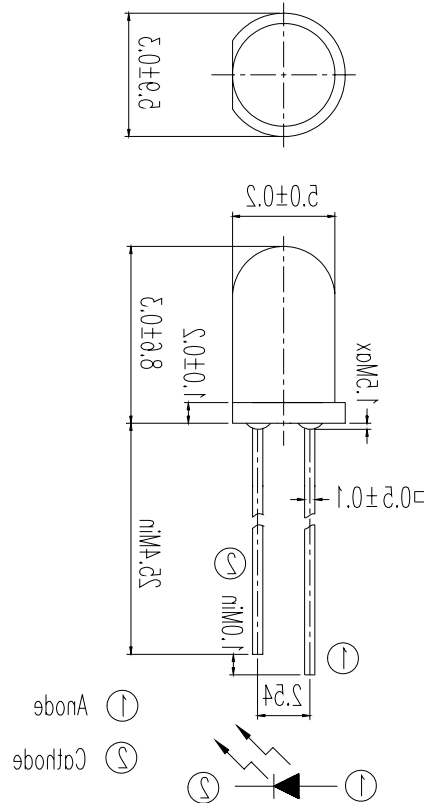
Applications

- Free air transmission system
- Optoelectronic switch
- Floppy disk drive
- Infrared applied system
- Smoke detector

Device Selection Guide

LED Part No.	Chip	Lens Color
	Material	
HIR	GaAlAs	Yellow

Package Dimensions



- Notes:** 1.All dimensions are in millimeters
2.Tolerances unless dimensions $\pm 0.25\text{mm}$

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Rating	Units
Continuous Forward Current	I_F	100	mA
Peak Forward Current	I_{FP}	1.0	A
Reverse Voltage	V_R	5	V
Operating Temperature	T_{opr}	$-40 \sim +85$	$^\circ\text{C}$
Storage Temperature	T_{stg}	$-40 \sim +85$	$^\circ\text{C}$
Soldering Temperature	T_{sol}	260	$^\circ\text{C}$
Power Dissipation at(or below) 25 $^\circ\text{C}$ Free Air Temperature	P_d	150	mW

Notes: *1: I_{FP} Conditions--Pulse Width $\leq 100 \mu\text{s}$ and Duty $\leq 1\%$.

*2:Soldering time ≤ 5 seconds.

Electro-Optical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Radiant Intensity	Ee	I _F =20mA	7.8	15	--	mW/sr
		I _F =100mA Pulse Width ≤ 100 μs ,Duty ≤ 1%	--	140	--	
		I _F =1A Pulse Width ≤ 100 μs ,Duty ≤ 1%.	--	950	--	
Peak Wavelength	λ _p	I _F =20mA	--	850	--	nm
Spectral Bandwidth	Δλ	I _F =20mA	--	45	--	nm
Forward Voltage	V _F	I _F =20mA		1.45	1.65	V
		I _F =100mA Pulse Width ≤ 100 μs ,Duty ≤ 1%	--	1.80	2.40	
		I _F =1A Pulse Width ≤ 100 μs ,Duty ≤ 1%.	--	4.10	5.25	
Reverse Current	I _R	V _R =5V	--	--	10	μA
View Angle	2θ _{1/2}	I _F =20mA	--	17	--	deg

Typical Electro-Optical Characteristics Curves

Fig.1 Forward Current vs.
Ambient Temperature

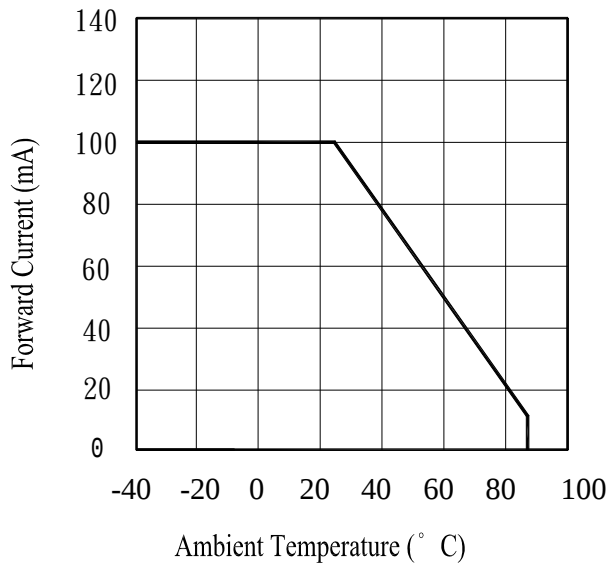


Fig.2 Spectral Distribution

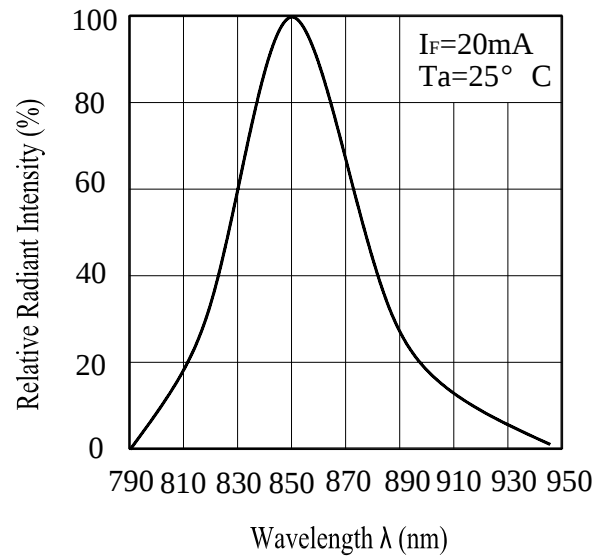


Fig.3 Peak Emission Wavelength
Ambient Temperature

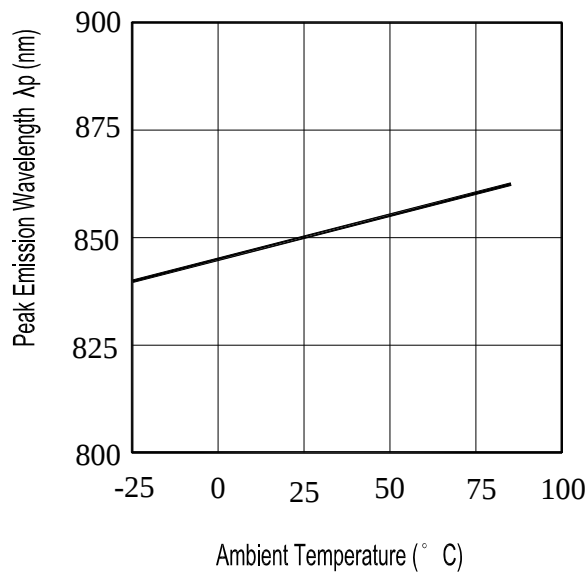
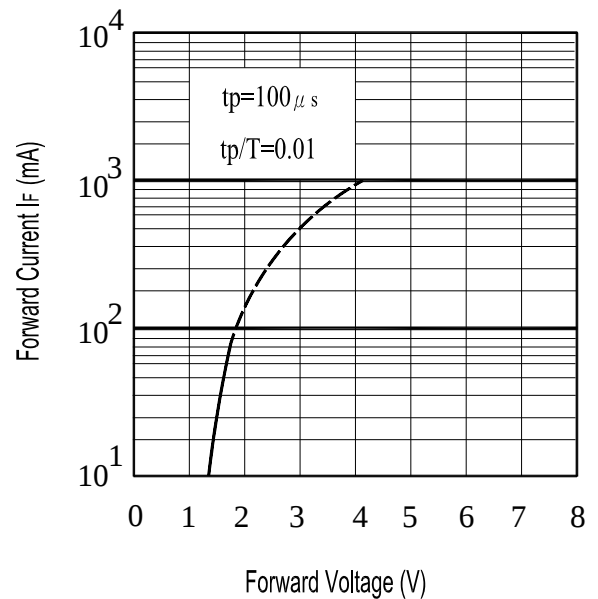


Fig.4 Forward Current
vs. Forward Voltage



Typical Electro-Optical Characteristics Curves

Fig.5 Relative Intensity vs.
Forward Current

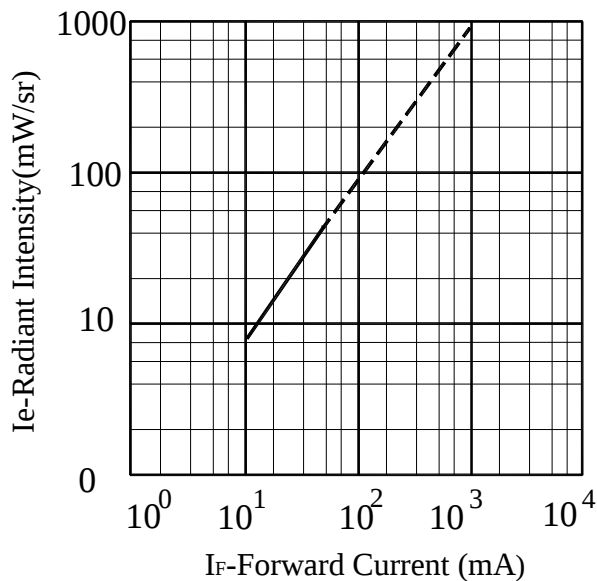


Fig.6 Relative Radiant Intensity vs.
Angular Displacement

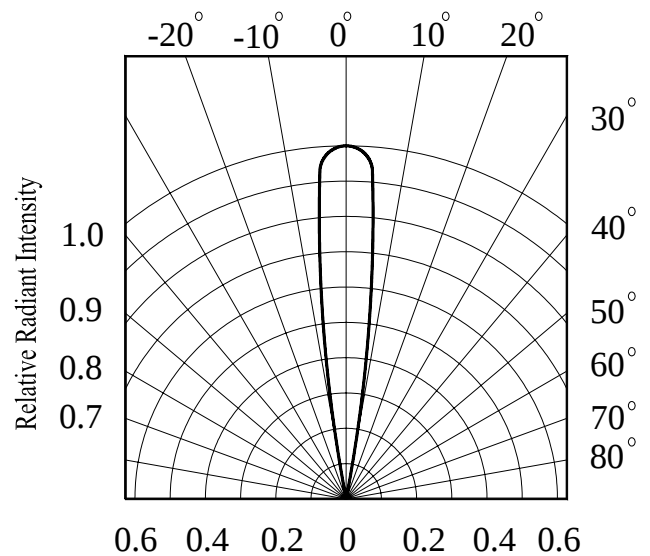


Fig.7 Relative Intensity vs.
Ambient Temperature(°C)

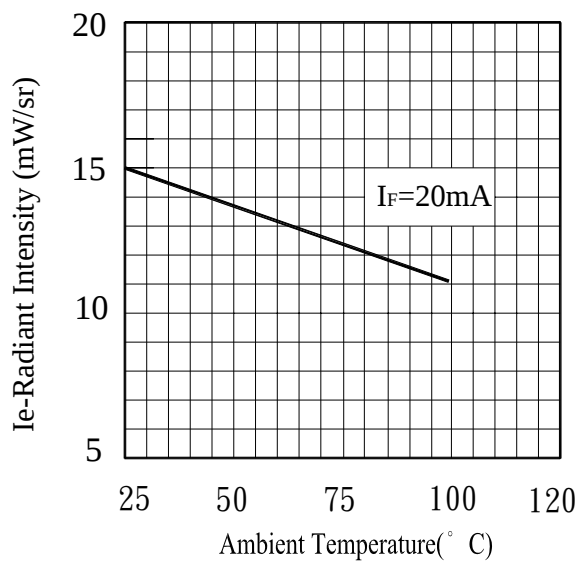
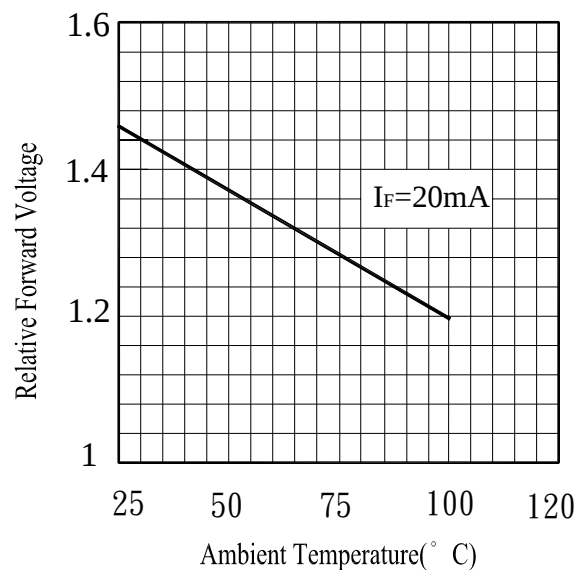


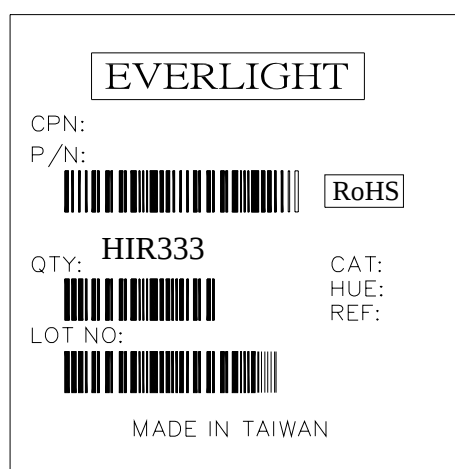
Fig.8 Forward Voltage vs.
Ambient Temperature(°C)



Packing Quantity Specification

1.500PCS/1Bag , 5Bags/1Box

2.10Boxes/1Carton

Label Form Specification

CPN: Customer's Production Number

P/N : Production Number

QTY: Packing Quantity

CAT: Ranks

HUE: Peak Wavelength

REF: Reference

LOT No: Lot Number

MADE IN TAIWAN: Production Place

Notes

1. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification.
2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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